

General Description

The AGM65R640D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

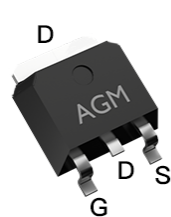
Application

- Electronic Ballast
- Electronic Transformer
- Switch Mode Power Supply

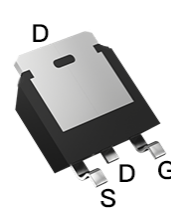
Product Summary

BVDSS	$R_{DS(ON)}$	ID
650V	0.57 Ω	7.0A

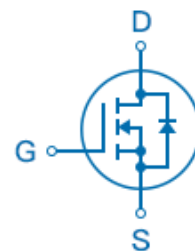
TO-252 Pin Configuration



Top View



Bottom View



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM65R640D	AGM65R640D	TO-252	330mm	16mm	2500

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	650	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	7.0	A
	Drain Current-Continuous(Tc=100°C)	4.4	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	28	A
PD	Maximum Power Dissipation(Tc=25°C)	61	w
	Maximum Power Dissipation(Tc=100°C)	24	w
EAS	Avalanche energy (Note 3)	147	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	62	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	2.05	°C/W

Table 3. Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	650	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=650V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	2.0	--	4.0	V
gFS	Forward Transconductance	VDS=15V,ID=3.5A	--	--	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=3.5A	--	0.57	0.64	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=100V,VGS=0V, F=1MHZ	--	423	--	pF
Coss	Output Capacitance		--	20	--	pF
Crss	Reverse Transfer Capacitance		--	0.8	--	pF
Rg	Gate resistance	f=1.0MHz	--	3.5	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VDD=325V, VGS=10V ID=7A,RGEN=25Ω	--	11	--	nS
tr	Turn-on Rise Time		--	30	--	nS
td(off)	Turn-Off Delay Time		--	28	--	nS
tf	Turn-Off Fall Time		--	24	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=520V, ID=7A	--	13	--	nC
Qgs	Gate-Source Charge		--	4.3	--	nC
Qgd	Gate-Drain Charge		--	6.7	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	7.0	A
VSD	Forward on Voltage	VGS=0V,ISD=7A	--	--	1.4	V
trr	Reverse Recovery Time	VGS=0V,VR=50V IS=7A,dI/dt=100A/μs	--	236	--	ns
Qrr	Reverse Recovery Charge		--	2.2	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T_J=25°C

典型特性曲线

图 1. 输出特性

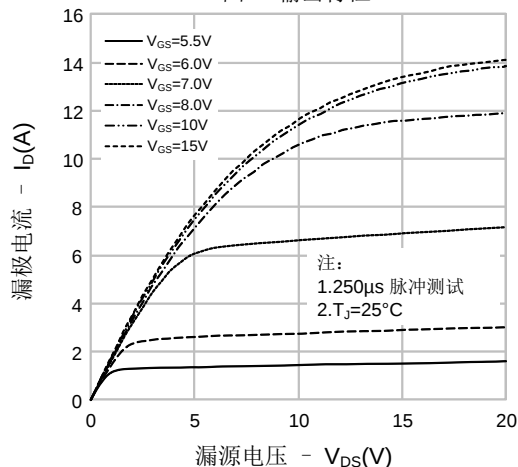


图 2. 输出特性

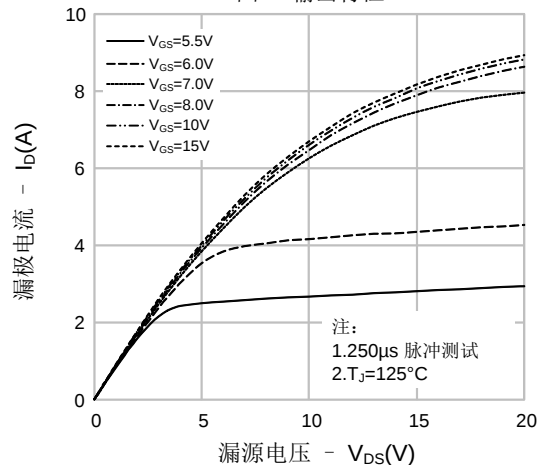


图 3. 传输特性

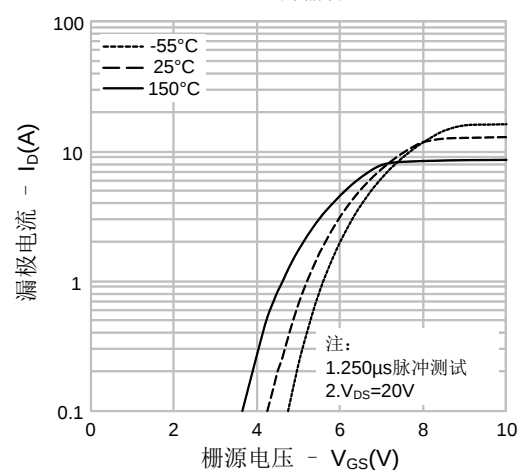


图 4. 导通电阻vs.漏极电流

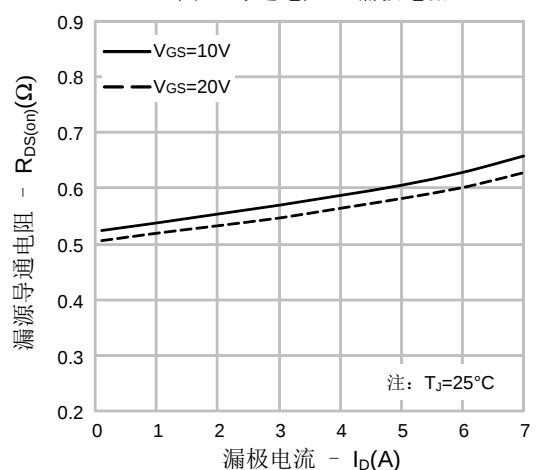


图 5. 导通电阻vs.漏极电流

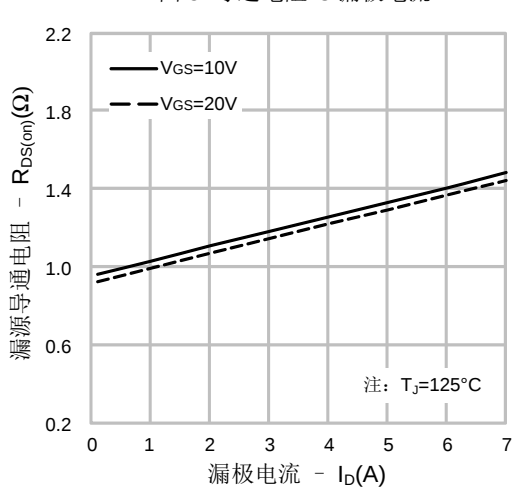
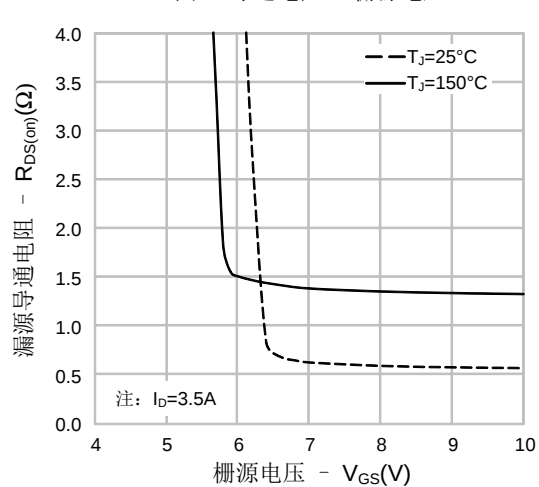


图 6. 导通电阻vs.栅源电压



典型特性曲线

图 7. 开启电压vs.温度特性

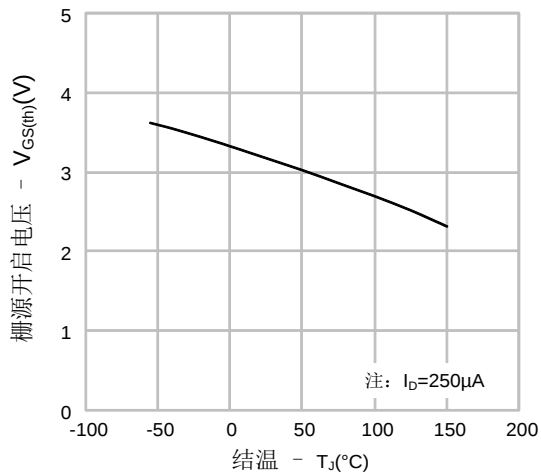


图 8. 体二极管正向压降vs. 源极电流、温度

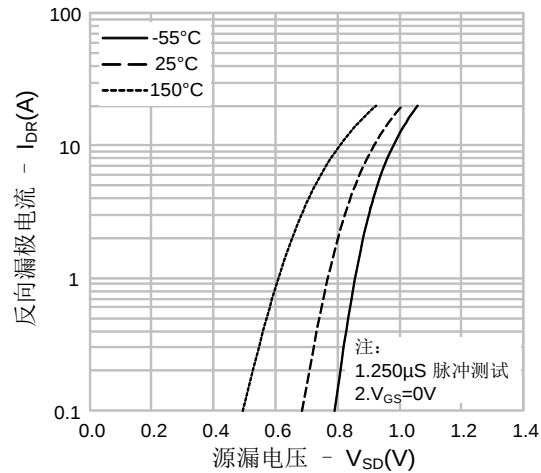


图9. 电容特性

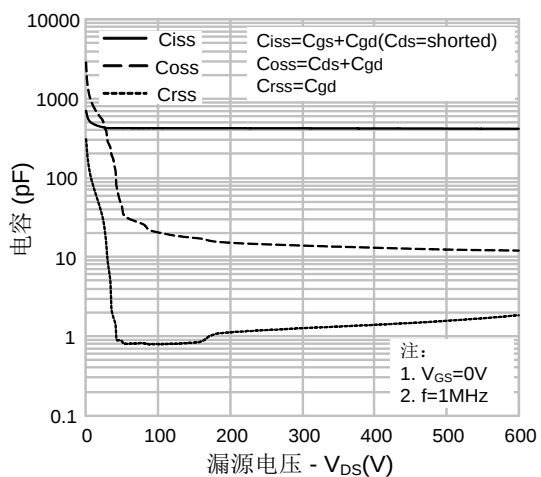


图 10. 电荷量特性

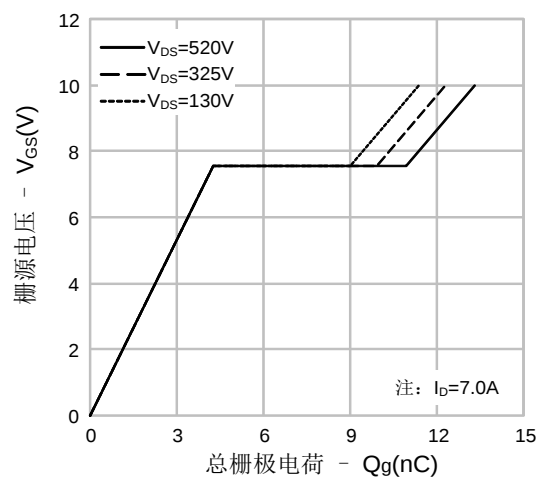


图 11. 击穿电压vs.温度特性

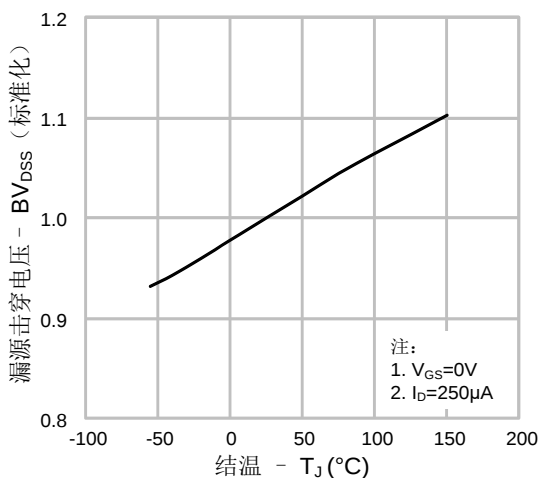
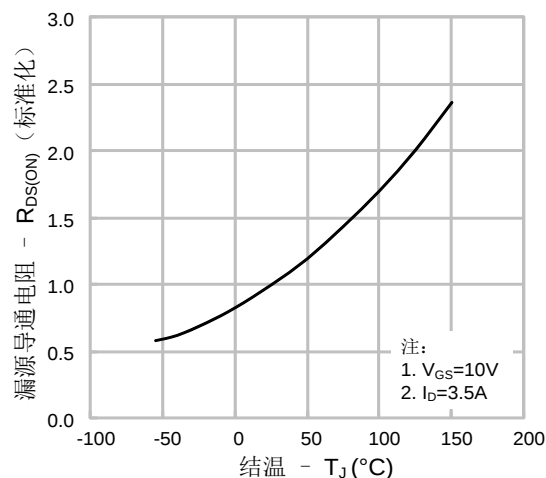


图 12. 导通电阻vs.温度特性



典型特性曲线

图 13-1. 最大安全工作区域(SVS65R640FJDD4)

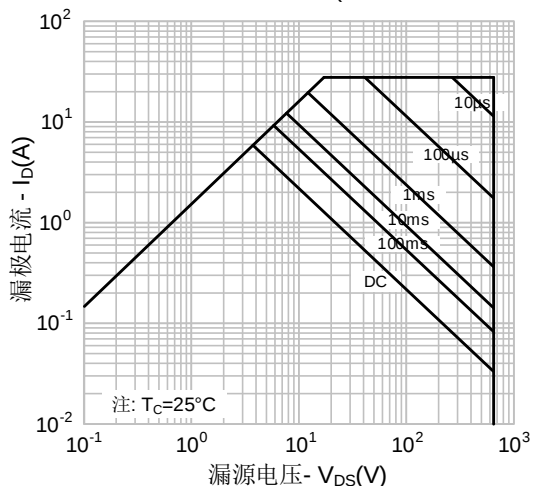


图 13-2. 最大安全工作区域(SVS65R640DD4)

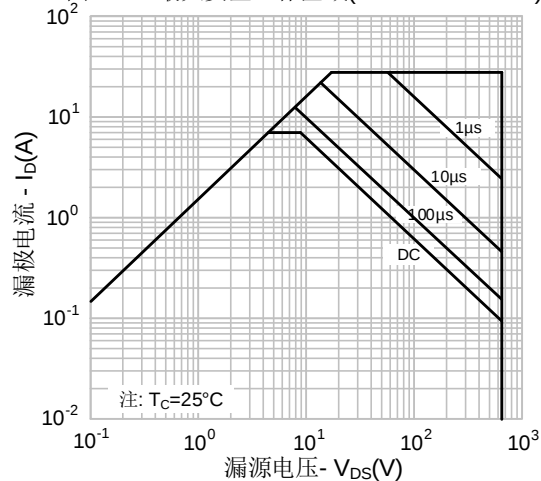


图14-1. 耗散功率vs.温度(SVS65R640FJDD4)

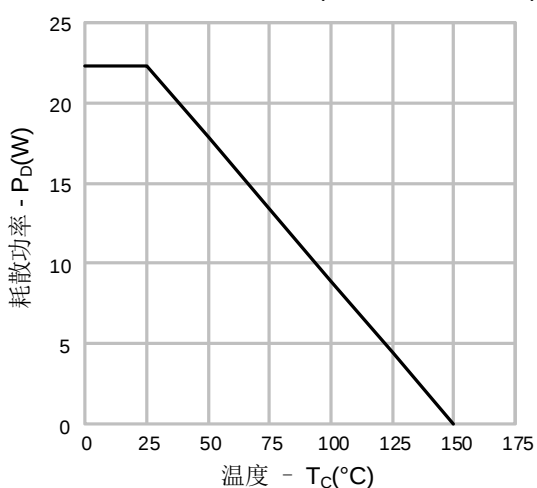


图14-2. 耗散功率vs.温度(SVS65R640DD4)

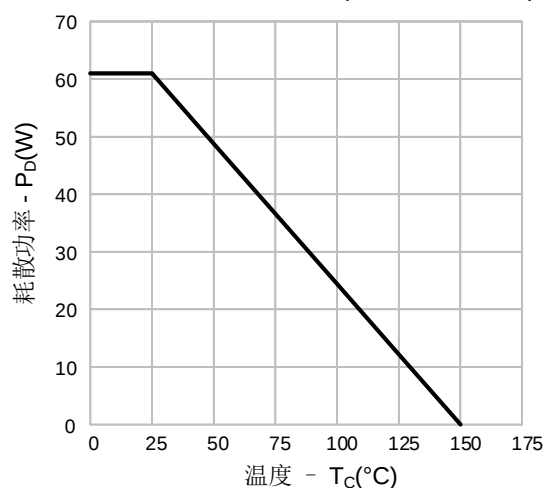


图15.漏极电流 vs. 壳温

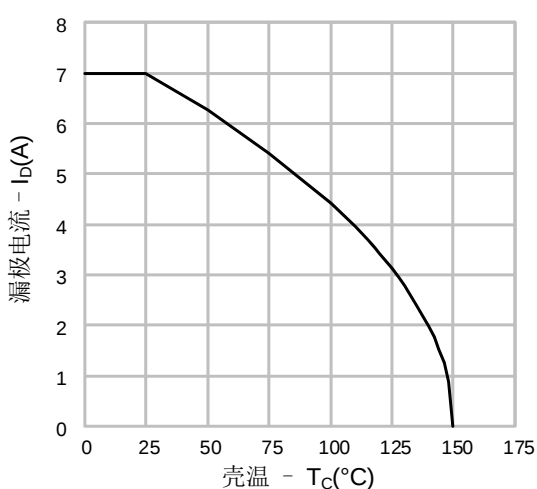
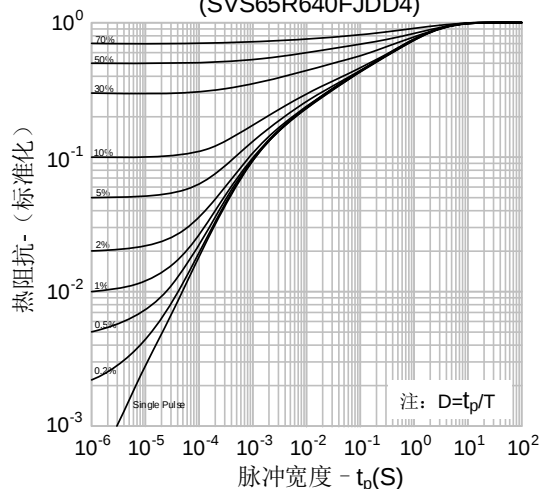
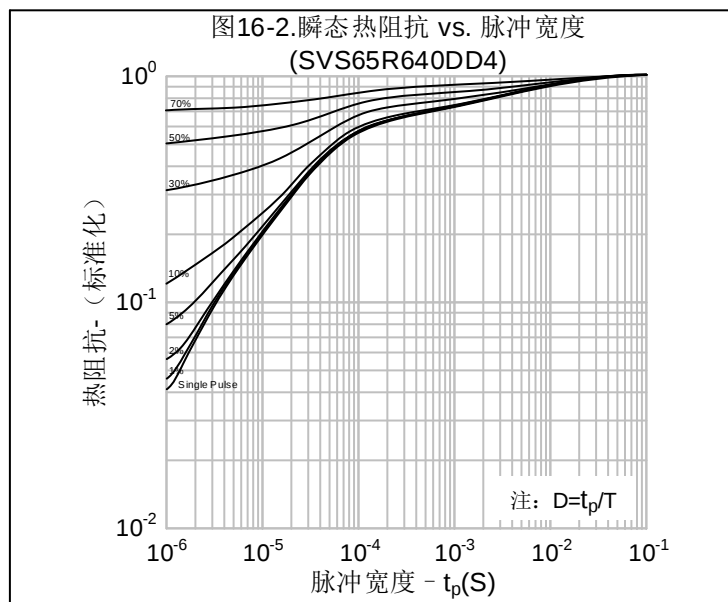


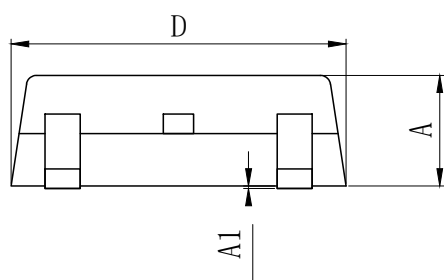
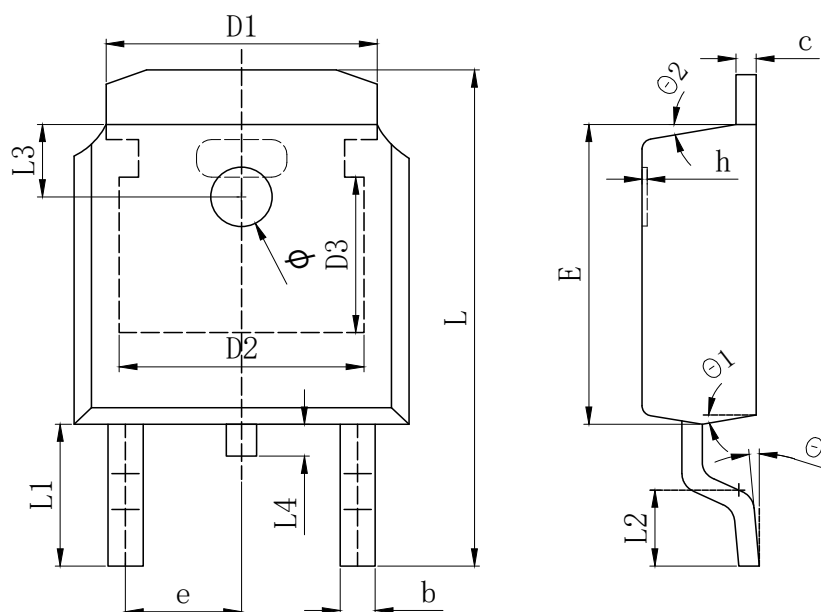
图16-1.瞬态热阻抗 vs. 脉冲宽度 (SVS65R640FJDD4)



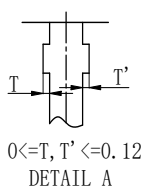
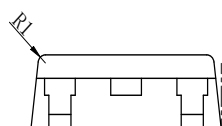
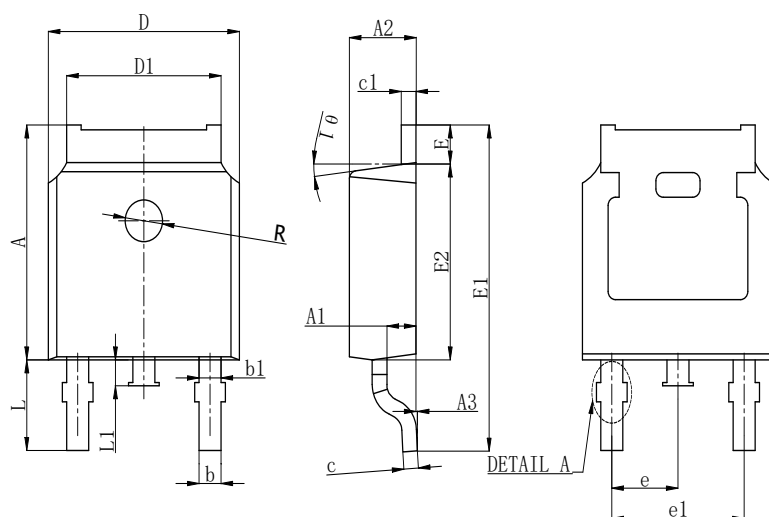
典型特性曲线



TO-252 Package Outline Data



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c (电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ 1	9° TYP		
θ 2	9° TYP		



0<=T, T' <=0.12
DETAIL A

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	7.050	7.100	7.150
A1	0.960	1.010	1.060
A2	2.250	2.300	2.350
A3	0.000	0.050	0.100
b	0.760REF.		
b1	1.000REF.		
c	0.508REF.		
c1	0.508REF.		
D	6.550	6.600	6.650
D1	5.220	5.320	5.420
E	0.950	1.000	1.050
E1	9.700	9.900	10.100
E2	6.050	6.100	6.150
e	2.286BSC		
e1	4.572REF.		
L	2.650	2.800	2.950
L1	0.700	0.800	0.900
θ 1	7° REF.		
R	1.300REF.		
R1	0.250REF.		

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